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**BiTS**

Workshop **上海** Shanghai

October 21, 2015

**Archive - Session 2**

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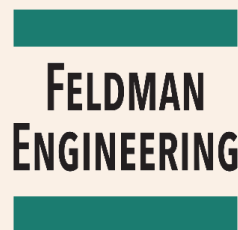
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## Session 2

Frank Zhou  
Session Chair

## BiTS Shanghai

### East Meets West

#### **"WLP Probing Technology Opportunity and Challenge"**

Clark Liu - PowerTech Technology Inc.

#### **"Pushing the Envelope in DFM (Design for Manufacturing) for 0.2mm Pitch WLCSP Socket"**

Colin Koh - Test Tooling Solutions Group

#### **"Signal Integrity & Impacts by Connector Structures"**

Jiachun (Frank) Zhou - Smiths Connectors

#### **"LPDDR4 Signal & Power Performance Optimization By Hardware"**

Yuanjun Shi - TwinSolution Technology

# Signal Integrity & Impacts by Connector Structures

**Dr. Jiachun Zhou (Frank), Dexian Liu**  
**Prof. Ling Sun**  
**Smiths Connectors, Nantong University**



2015 BiTS Workshop  
Shanghai  
October 21, 2015

smiths connectors



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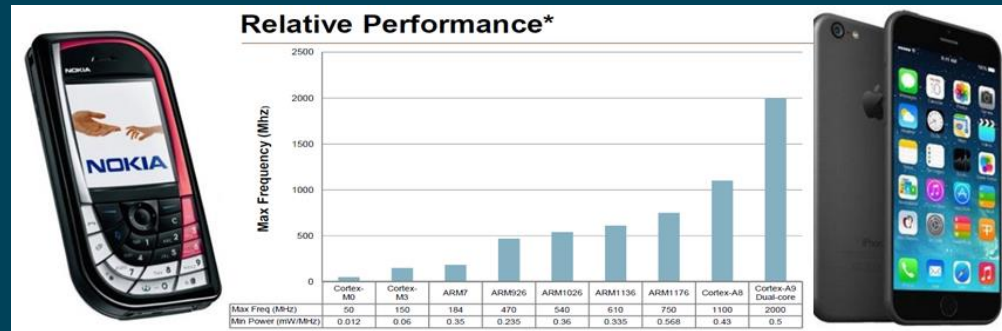
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- Why Signal Integrity?
- Signal Integrity Basics
- Signal Integrity Characteristics
- Connector's Structures & Signal Integrity
- Summary

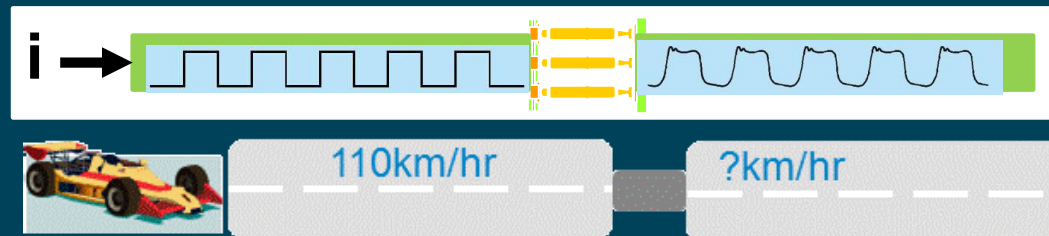
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## Why Signal Integrity (SI)?

- Digital world moves to higher frequency.



- Interconnect subsystems impact signal propagation significantly due to materials properties and mechanical structures.



## What is Signal Integrity?

- **Signal integrity refers to all the problems that arise in high-speed products due to the interconnects.**  
- from Eric Bogatin in “Signal Integrity”
- **Signal integrity is a set of measures to evaluate the quality of the electrical signal.**
- **Some of the main issues about SI are signal loss, ringing, crosstalk, ground bounce and power supply noise.**



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## Signal Integrity Basics

- Resistance at DC

$$R = \frac{V}{I} \quad R = \frac{\rho l}{A}$$

$\rho$  = material bulk resistivity

$l$  = conductor length

$A$  = conductor cross section area

- Impedance at AC

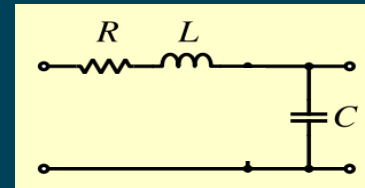
$$Z = \frac{V}{I}$$

- Characteristic Impedance

$$Z_0 = \sqrt{\frac{L}{C}}$$

$L$  = inductance

$C$  = capacitance



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## SI Characteristics-1

- Signal has losses when going through connector
  - Insertion Loss: signal power loss resulting from the insertion of a device in a transmission line
  - Return Loss: power loss in the signal returned or reflected by a discontinuity in a transmission line
  - Bandwidth: the signal frequency transmitted without significant loss (or at allowable insertion loss)

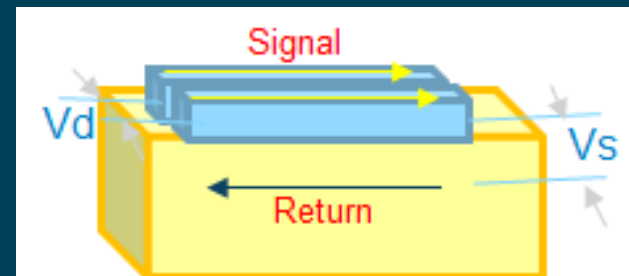
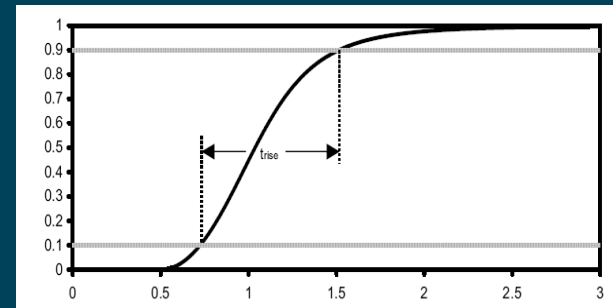
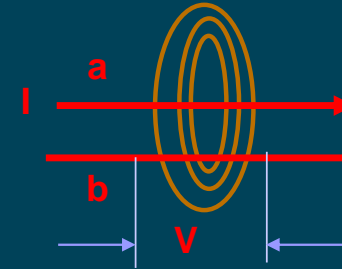


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## SI Characteristics-2

- Cross Talk
  - Induced noise to “b” line by the signal in “a”
$$V_{\text{noise}} = M \, di/dt$$

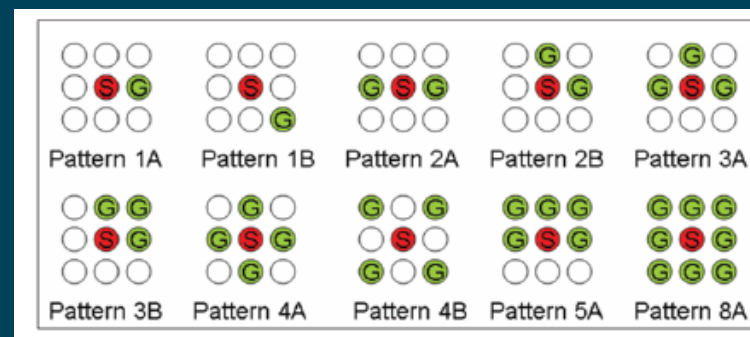
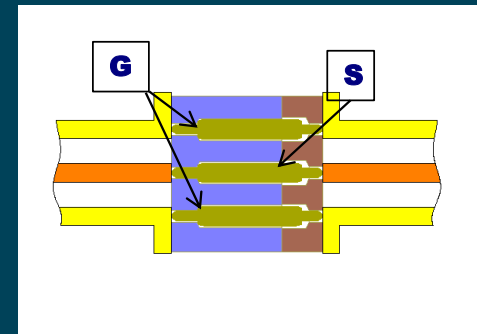
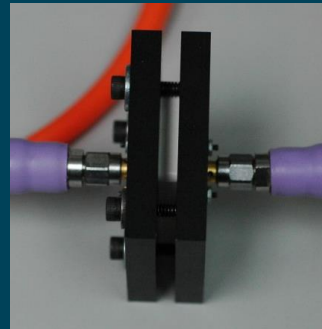
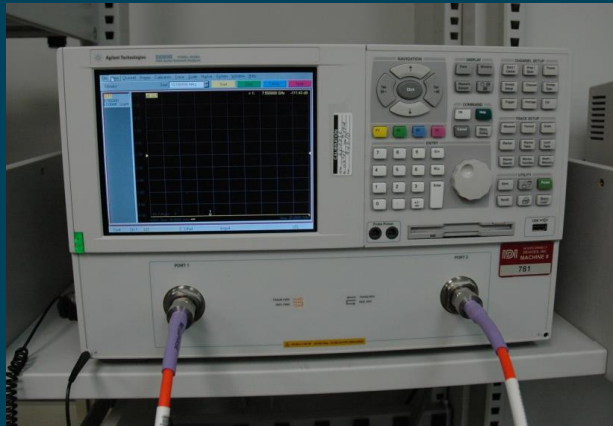
M: Mutual inductance of 2 wires
- Rise Time
  - The time required for a pulse to rise from 10% to 90% of its steady value
- Single ended & differentials
  - Single ended: measured between the signal and return path
  - Differentials: measured between the two signal lines in a different pair



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## SI Measurements Set Up

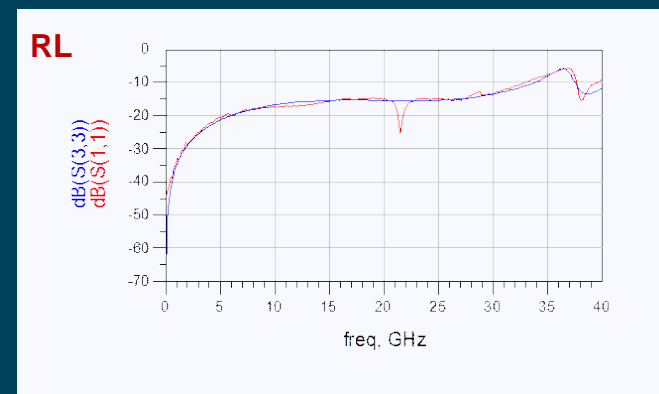
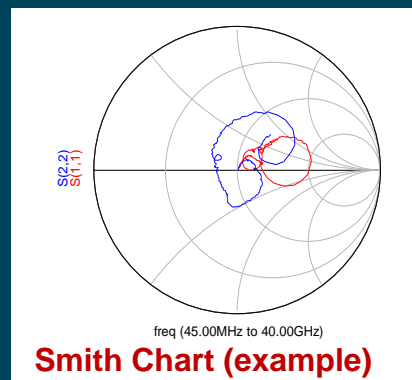
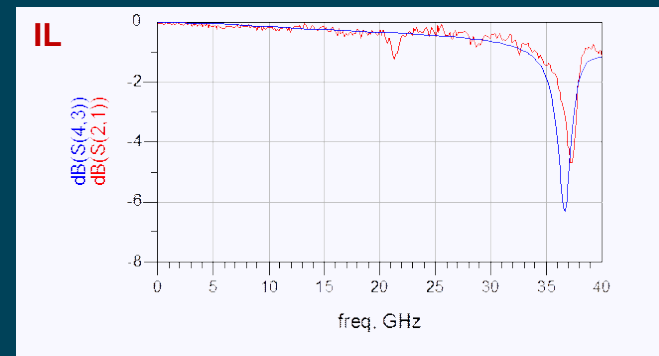
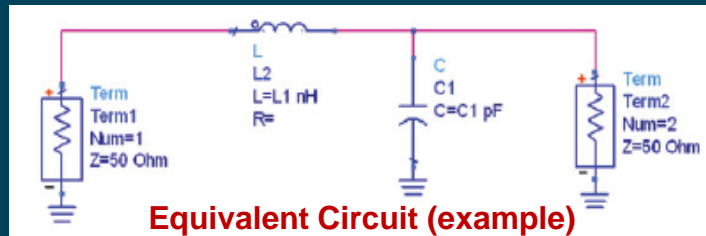
- SI measurement set up includes:
  - Vector Network Analyzer
  - Connector fixture with different patterns



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## SI Measurements Method

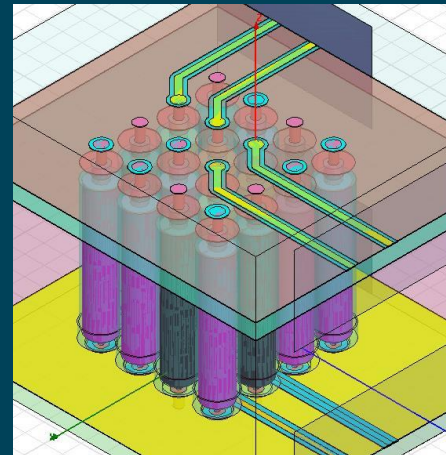
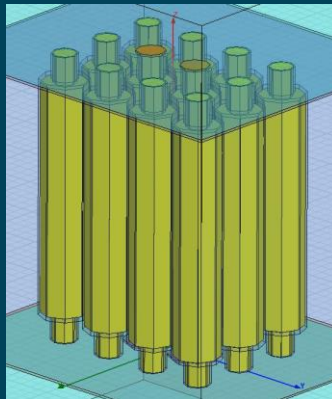
- Measure IL, RL and Smith Chart
- Use equivalent circuit & ADS software to simulate IL, RL and calculate L, C



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## SI Simulation

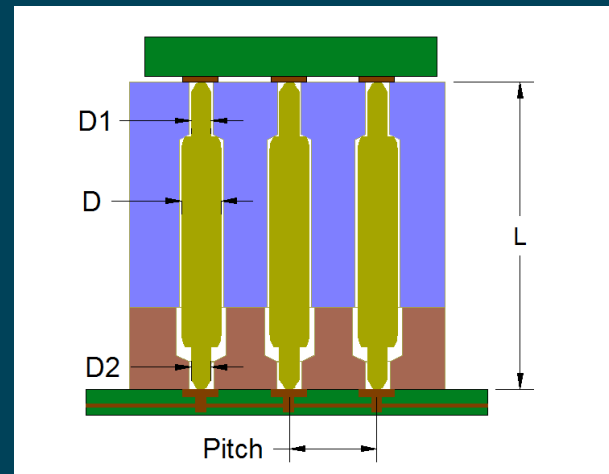
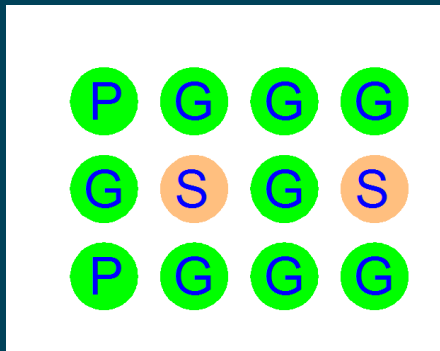
- Several software, e.g. HFSS, used in SI simulation
- Physical model following signal/ground pin pattern
- Connector geometry may be simplified by removing complex features, such as spring
- Simulation results include IL, RL, Zo, Rise time etc.



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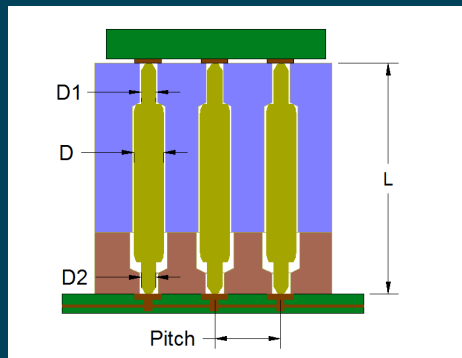
## Connector Structures

- Connect basic structures affecting SI
  - Connector length,  $L$ , from signal entrance to exit
  - Connector diameter
  - Connector housing material & structures
  - Connector layout pattern

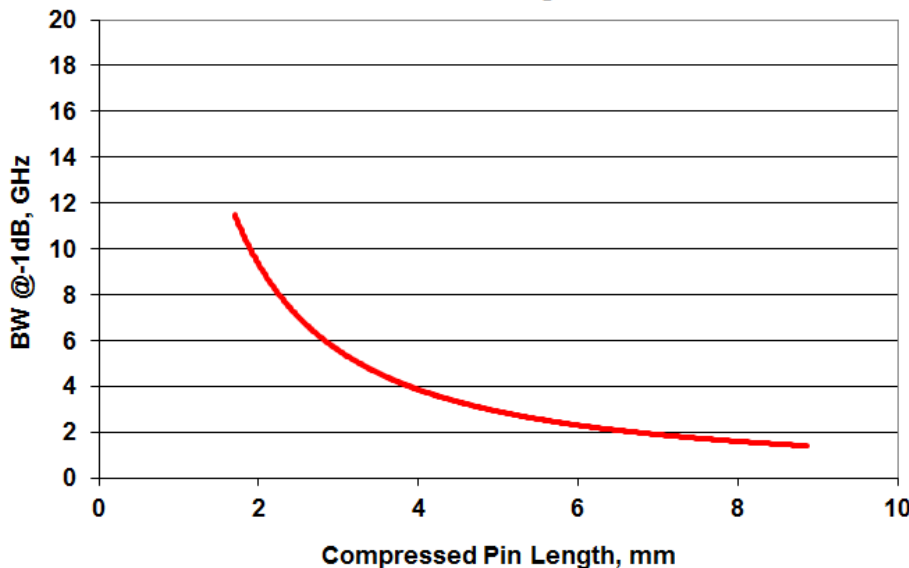


## SI Performance: Pin Length

- Method: use RF measurements of over 100 different pins from various pin makers to do statistics analysis
- Results: BW @ -1dB increases after pin length < 3mm



### Bandwidth vs. Pin Length (test status)

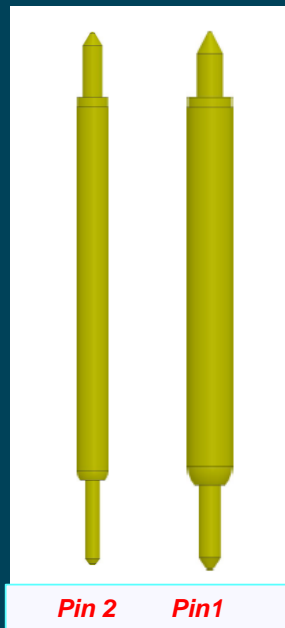




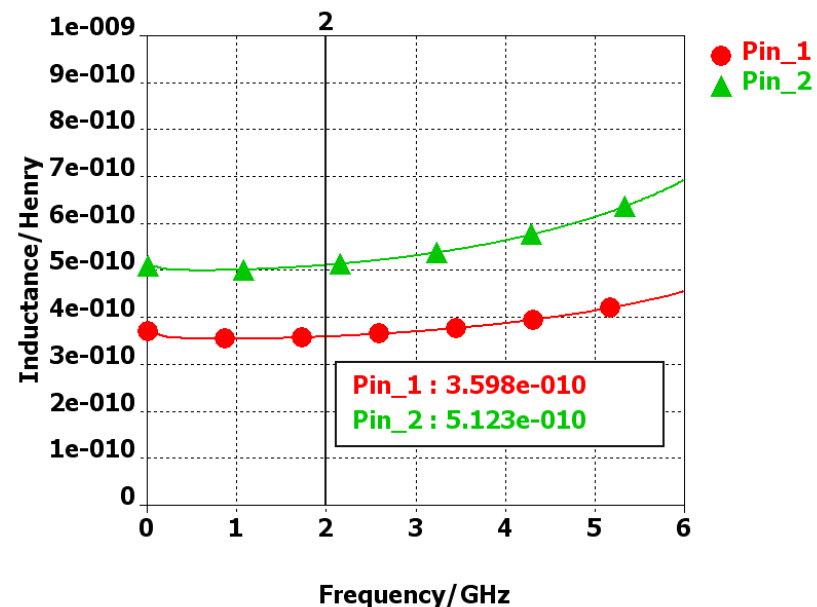
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## SI Performance: Pin Diameter

- Pin 1: larger diameter has less Inductance
- Pin 2: smaller diameter has higher Inductance



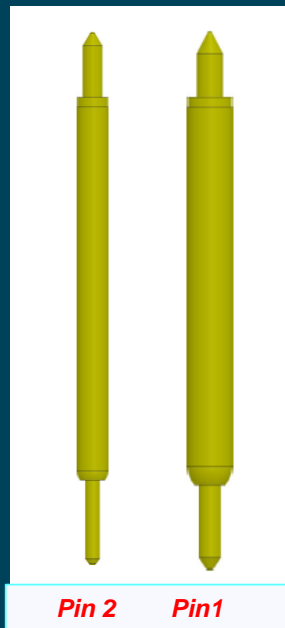
### Inductance vs. Diameter vs. Frequency



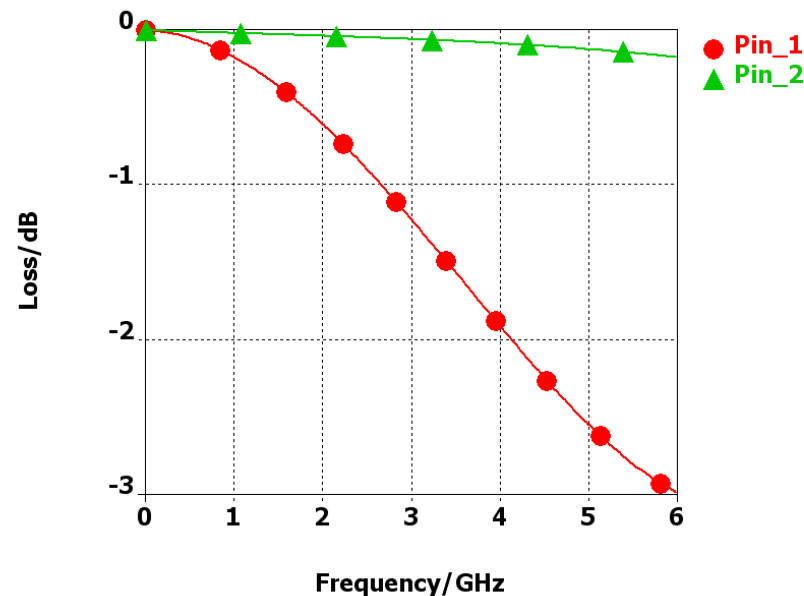
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## SI Performance: Pin Diameter

- Pin 1: larger diameter has low Bandwidth
- Pin 2: smaller diameter has high Bandwidth (or less signal loss)



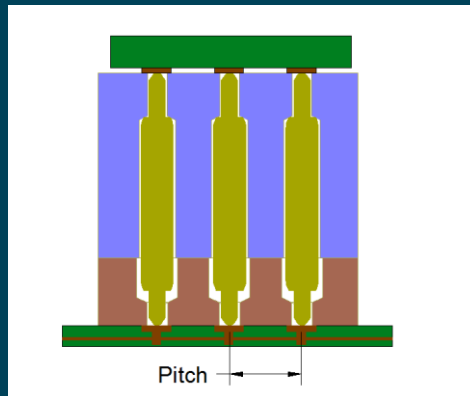
### Bandwidth vs. Diameter vs. Frequency



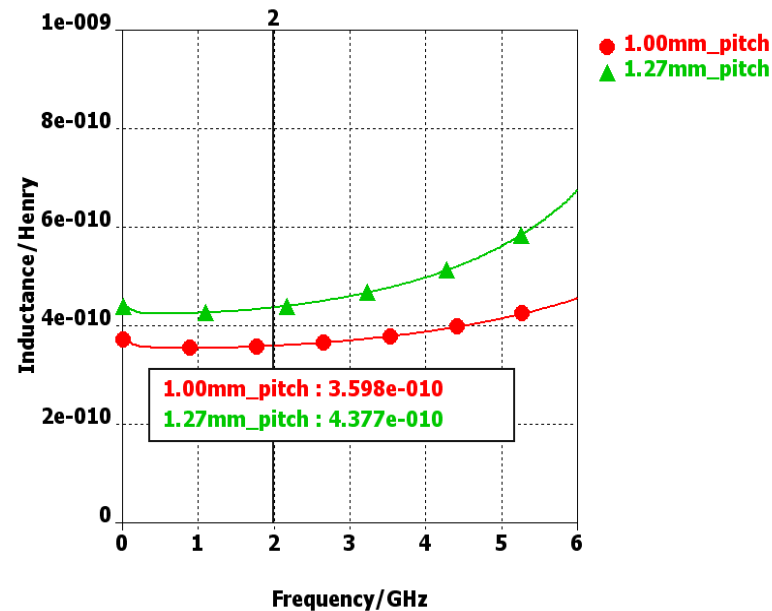
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## SI Performance: Pitch

- Smaller pitch (same pin): has lower Inductance
- Larger pitch (same pin): has higher Inductance



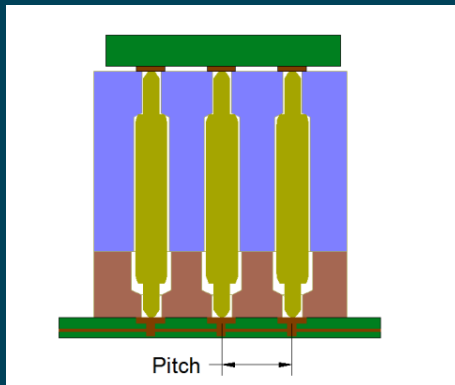
### Inductance vs. Pitch vs. Frequency



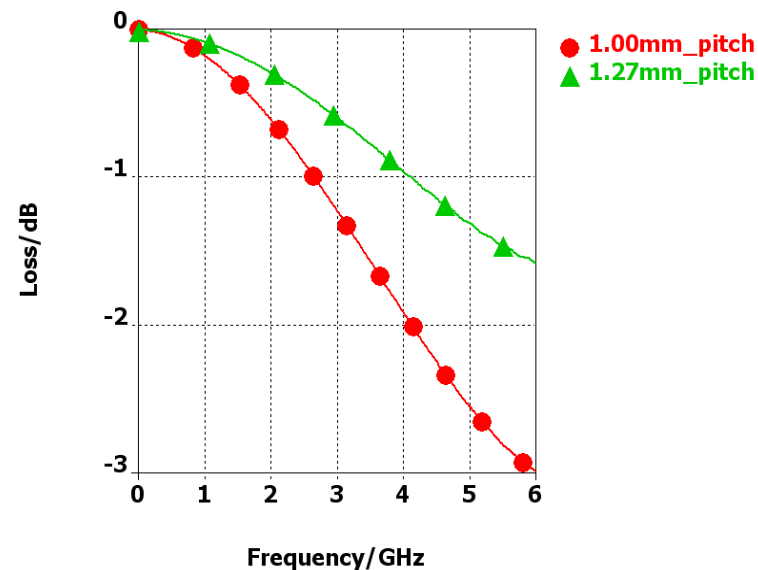
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## SI Performance: Pitch

- Smaller pitch (same pin): has lower Bandwidth;
- Larger pitch (same pin): has higher Bandwidth.



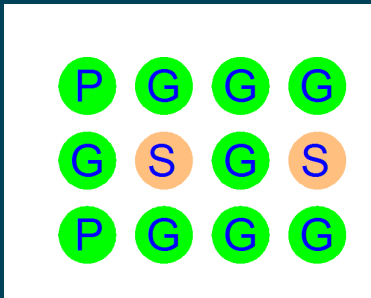
### BW vs. Pitch



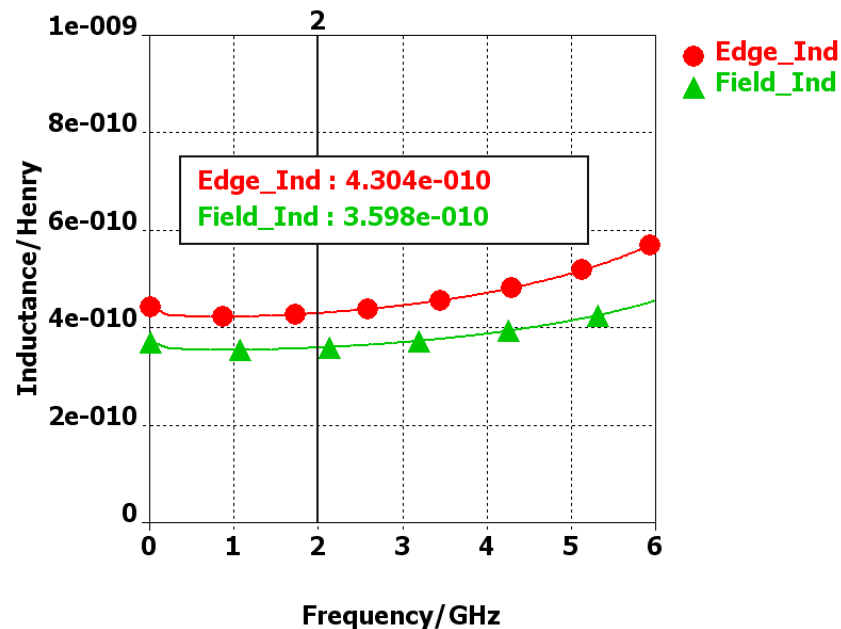
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## SI Performance: Edge vs. Field

- Pin at edge: has higher Inductance
- Pin at field: has lower Inductance



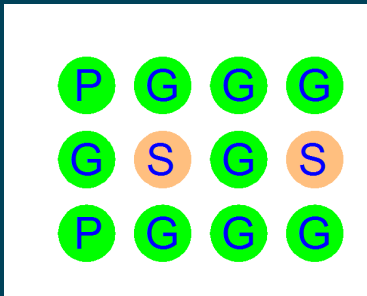
### Inductance vs. Pin location vs. Frequency



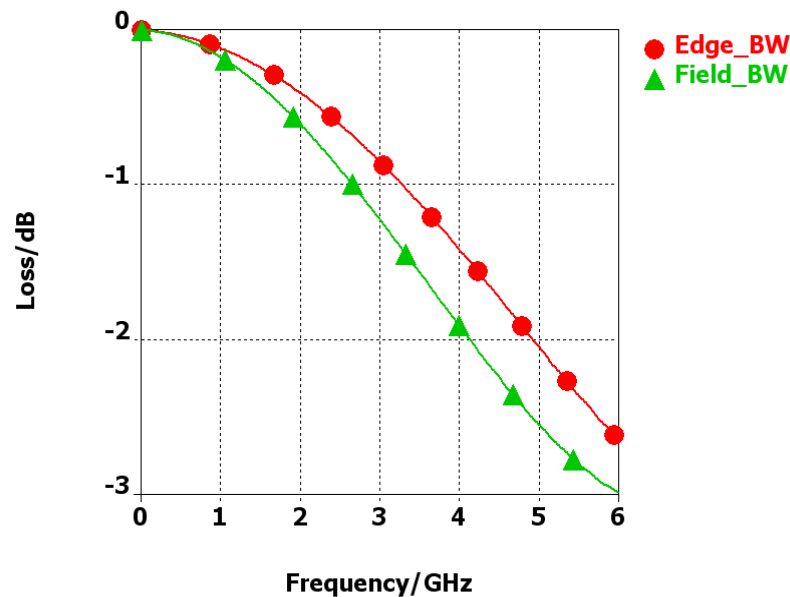
# BiTS Shanghai 2015

## SI Performance: Edge vs. Field

- Pin at edge: has higher Bandwidth
- Pin at field: has lower Bandwidth



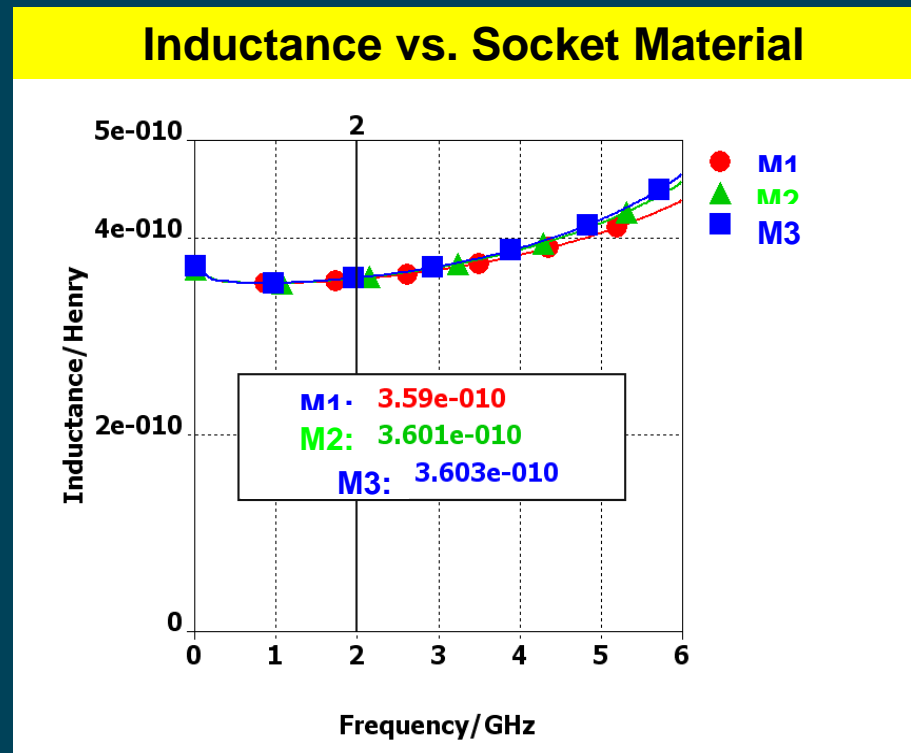
### BW vs. Pin Location vs. Frequency



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## SI Performance: Socket Material

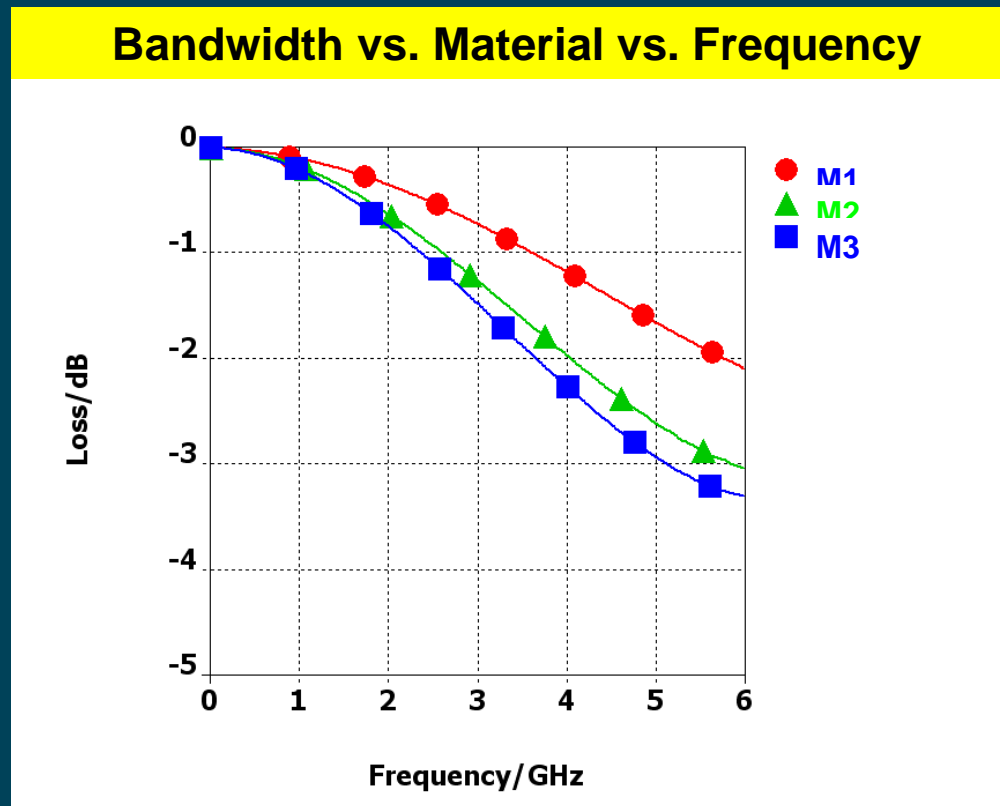
- Socket materials: has little impacts on Inductance



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## SI Performance: Socket Material

- Socket materials: has greater impacts on Bandwidth





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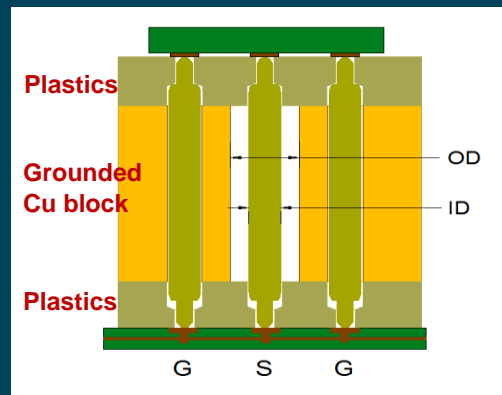
## SI Performance: Coaxial Structure

- Principle: Impedance is correlated to signal pin diameter and grounded body following formula:

$$Z_o = \frac{138}{\sqrt{\epsilon_r}} \log_{10} \frac{D}{d}$$

$\epsilon_r$ : Relative dielectric constant of insulator in Cu & connector

- Application: impedance controlled structure to be 50Ω, bandwidth >15GHz (using optimal structure)



Signal Integrity & Impacts by Connector Structures

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## Summary

### Two methods to learn connector signal integrity

- Use VNA & test fixture to measure IL, RL, BW, etc.
- Use HFSS or other software to simulate

### Connector SI is mostly affected by its structures

- Length, shorter pin with better SI
- Diameter, small diameter with higher BW but larger L
- Location, edge pin has better SI (most high frequency signal pins at edge)
- House material, low dielectric constant has better SI
- Coaxial structure, control the impedance for better SI

**Optimal connector design needs to consider both SI, mechanical behavior, manufacturing feasibility**